L Number	Hits	Search Text	DB	Time stamp
1	2	("4942554").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/06/18 16:46
5	3	6214653.URPN.	IBM_TDB USPAT	2003/06/18 16:53
6	12	("5244828"   "5258318"   "5373803"   "5399507"   "5493137"   "5508219"   "5585284"   "5830784"   "5891763"   "5930638"   "5956597"   "6015745").PN.	USPAT	2003/06/18 16:53
10	2	(amorphizing amorphization amorphized) with periphery with trench and (438/6 257/\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/18 17:12
16	0	(amorphous) with (ion implant implantation implanting implanted) with periphery with trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/18 17:13
17	6	(amorphizing amorphization amorphized) with (trench groove recess recessed grooved) with periphery	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/18 17:20
18	4	((amorphizing amorphization amorphized) with (trench groove recess recessed grooved) with periphery) not ((amorphizing amorphization amorphized) with periphery with trench and (438/6 257/\$6))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 17:14
22	3	(amorphizing amorphization amorphized amorphous) with (ion implant implantation implanting implanted) and ("4676847"   "5543348"   "5641694"   "5843820"   "5893735"   "5998821"   "6093614"   "6207493"   "6214653"   "6238967").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 17:17
25	45	(amorphizing amorphization amorphized) with (trench groove recess recessed grooved)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/18 17:20
55	1017	trench with (etch etching) and ((oxide dioxide) and nitride) with mask and removing with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/18 17:52
56	1232	trench with (etch etching) and ((oxide dioxide) and nitride) with mask and removing with mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/18 17:56
57	1389	(438/222,226,357,360,363,429,442,for.167,f		.2003/06/18 17:53
58	18	(trench with (etch etching) and ((oxide dioxide) and nitride) with mask and removing with mask) and ((438/222,226,357,360,363,429,442,for.167,	USPAT; US-PGPUB; EPO; JPO;	2003/06/18 17:54 IS.)
59	152	trench with (etch etching) and ((oxide dioxide) and nitride) with mask and removing with mask and (mask with etch adj back etchback)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 17:56

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60	156	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2003/06/18
		dioxide) and nitride) with mask and	US-PGPUB;	17:57
		removing with mask and ((oxid nitrid	EPO; JPO;	
		dioxide mask) with etch adj back	DERWENT;	
		etchback)	IBM_TDB	
61	231		USPAT;	2003/06/18
		dioxide) and nitride) with mask and	US-PGPUB;	17:57
		removing with mask and ((oxide nitrid	EPO; JPO;	
		dioxide mask) with etch adj back	DERWENT;	
		etchback)	IBM TDB	
62	10	6074954.URPN.	USPĀT	2003/06/18
				18:18
63	15	("4755476"   "4895810"   "5120668"	USPAT	2003/06/18
		"5160407"   "5182234"   "5229315"		18:19
		"5256583"   "5283201"   "5318665"		
		"5374584"   "5449433"   "5453156"		
		"5492850"   "5656535"   "5731130").PN.		
_	1389	(438/222,226,357,360,363,429,442,for.167,f	byspat).ccls	.2003/06/18
1		( , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	17:53
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	21	(amorphizing amorphization amorphized	USPAT;	2003/06/18
		amorphous) with (ion implant implantation	US-PGPUB;	17:16
		implanting implanted) and	EPO; JPO;	
		((438/222,226,357,360,363,429,442,for.167,		s.)
		((450)222)220)301)300)300)123)112)2011207)	IBM TDB	[ ]
l _	1	(amorphizing amorphization amorphized) and	USPAT;	2003/06/18
	1	((438/222,226,357,360,363,429,442,for.167,		
		((130),222,220,307,300,300,123,112,202,120.7	EPO; JPO;	,
			DERWENT;	,
			IBM TDB	
_	415	(amorphizing amorphization amorphized)	USPAT;	2003/06/18
	113	and (438/6 257/\$6)	US-PGPUB;	17:11
		ana (150, 0 251, 40,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	342	(amorphizing amorphization amorphized	USPAT;	2003/06/18
	0.5	amorphous) with (ion implant implantation	US-PGPUB;	17:21
	ļ	implanting implanted) and ((amorphizing	EPO; JPO;	
		amorphization amorphized) and (438/6	DERWENT;	
		257/\$6))	IBM TDB	
_	45	(amorphizing amorphization amorphized)	USPAT;	2003/06/18
		with (trench groove recess recessed	US-PGPUB;	17:51
		grooved)	EPO; JPO;	
1			DERWENT;	
1	1		IBM TDB	
_	227	((amorphizing amorphization amorphized)	USPAT;	2003/06/18
		and (438/6 257/\$6)) and (recrystal	US-PGPUB;	11:32
	1	crystal crystallize crystalization	EPO; JPO;	
		crystallizing recrystallize	DERWENT;	
	1	recrystalization recrystallizing anneal	IBM_TDB	
[	[	annealing annealling annealed) with	-	
	1	(amorphized amorphous)		
l <b>-</b>	192	((amorphizing amorphization amorphized	USPAT;	2003/06/18
1	1	amorphous) with (ion implant implantation	US-PGPUB;	11:32
		implanting implanted) and ((amorphizing	EPO; JPO;	
1		amorphization amorphized) and (438/6	DERWENT;	
		257/\$6))) and (((amorphizing	IBM_TDB	
		amorphization amorphized) and (438/6		
		257/\$6)) and (recrystal crystal		
	1	crystallize crystalization crystallizing		
		recrystallize recrystalization		
		recrystallizing anneal annealing	]	
		annealling annealed) with (amorphized		
		amorphous))	L	

-	182	(((amorphizing amorphization amorphized	USPAT;	2003/06/18
		amorphous) with (ion implant implantation	US-PGPUB;	11:33
		implanting implanted) and ((amorphizing	EPO; JPO;	
	l	amorphization amorphized) and (438/6	DERWENT;	
		257/\$6))) and (((amorphizing	IBM_TDB	
		amorphization amorphized) and (438/6		
		257/\$6)) and (recrystal crystal		
		crystallize crystalization crystallizing		
ŀ		recrystallize recrystalization		
		recrystallizing anneal annealing		
		annealling annealed) with (amorphized		
		amorphous))) not (((amorphizing		
-	140	amorphozphiomngmamphphedatwonhamorphched	USPAT;	2003/06/18
		emorphonecesitheceenedmylentedmplantation	US-PGPUB;	15:42
		imphemphingi impamotphizandom (amorphizedg	EPO; JPO;	
		amorphomatiwmthmorphizmdlanddimpBan6ation	DERWENT;	
		2mm/antingandplantmdrphiding	IBM TDB	
		4m439M22at206, a607r9M0zed3, 400, 4438f6r. 167,	$for.\overline{2}21).CCI$	s.)))
		257/\$6)) and (recrystal crystal		
		crystallize crystalization crystallizing		
		recrystallize recrystalization		
1		recrystallizing anneal annealing		
		annealling annealed) with (amorphized		
		amorphous))) not (((amorphizing		
İ		amorphization amorphized) with (trench		
		groove recess recessed grooved))		Ì
_	o	65am8FBhuRPNg amorphization amorphized	USPAT	2003/06/18
	Ĭ	amorphous) with (ion implant implantation		14:05
_	10	imaba68420 impha48848"and"5641694"	USPAT	2003/06/18
		758388202,22858937350,36359298242,for.167,	for.221).CCI	51.4:)05
		86693664Ming"600M498Ymed"62p4658"		-
		d6p38967hg. amposited) with amorphous		
-	554	trench with DRAm with isolation	USPAT;	2003/06/18
			US-PGPUB;	15:45
			EPO; JPO;	l i
			DERWENT;	
			IBM_TDB	
_	7	(trench with DRAm with isolation) and	USPAT;	2003/06/18
		conformal near (insulator oxide dioxide)	US-PGPUB;	15:43
		·	EPO; JPO;	
			DERWENT;	
			IBM TDB	
<b>-</b>	4	(trench with DRAm with isolation) and	USPAT;	2003/06/18
		conformal near (insulator oxide dioxide)	US-PGPUB;	15:44
		with trench	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	170	trench with DRAm with sti	USPAT;	2003/06/18
			US-PGPUB;	15:45
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	8	trench with DRAm near2 sti	USPAT;	2003/06/18
1			US-PGPUB;	15:46
			EPO; JPO;	
			DERWENT;	
			IBM TDB	l i
_	5.3	trench with DRAm near4 sti not (trench	USPAT;	2003/06/18
		with DRAm near2 sti)	US-PGPUB;	15:47
1		, , , , , , , , , , , , , , , , , , ,	EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
-	18	trench with DRAm and conformal near2	USPAT;	2003/06/18
1	1	(silicon near oxide)	US-PGPUB;	15:48
	[	,,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
L	<u> </u>	<u> </u>	<del></del>	L

	-	6	trench with DRAm and conformal near2 (silicon near oxide) with trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/18 15:48
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